

## 60V N-Channel Enhancement Mode Power MOSFET

|  |   |
|--|---|
| <p><b>General Description</b></p> <p>The STD35NF06 uses advanced trench technology and design to provide excellent <math>R_{DS(ON)}</math> with low gate charge. It can be used in a wide variety of applications.</p> <p><b>Features</b></p> <ul style="list-style-type: none"> <li>● <math>V_{DS} = 60V, I_D = 35A</math></li> <li>● <math>R_{DS(ON)}, 20m\Omega</math> (Typ) @ <math>V_{GS} = 10V</math></li> <li>● <math>R_{DS(ON)}, 16m\Omega</math> (Typ) @ <math>V_{GS} = 4.5V</math></li> <li>● Advanced Trench Technology</li> <li>● Excellent <math>R_{DS(ON)}</math> and Low Gate Charge</li> <li>● Lead free product is acquired</li> </ul> <p><b>Application</b></p> <ul style="list-style-type: none"> <li>● Load Switch</li> <li>● PWM Application</li> <li>● Power management</li> </ul> | <div style="text-align: center;"> <p>TO-252(DPAK) top view</p> </div> <div style="text-align: center; margin-top: 20px;"> <p>Schematic Diagram</p> </div> |
|--|---|

### Absolute Maximum Ratings(TA=25°C unless otherwise noted)

| Parameter                                 |          | Symbol    | Value       | Unit |
|---|----------|-----------|-------------|------|
| Drain-Source Voltage                      |          | $V_{DS}$  | 60          | V    |
| Gate-Source Voltage                       |          | $V_{GS}$  | ±20         | V    |
| Drain Current-Continuous <sup>Note3</sup> | TC=25°C  |           | 35          | A    |
|   | TC=100°C |           | 25          | A    |
| Drain Current-Pulsed <sup>Note1</sup>     |          | $I_{DM}$  | 140         | A    |
| Avalanche Energy <sup>Note4</sup>         |          | $E_{AS}$  | 72          | mJ   |
| Maximum Power Dissipation                 | TC=25°C  | $P_D$     | 105         | W    |
| Storage Temperature Range                 |          | $T_{STG}$ | -55 to +150 | °C   |
| Operating Junction Temperature Range      |          | $T_J$     | -55 to +150 | °C   |

### Thermal Resistance

| Parameter                            | Symbol          | Min. | Typ. | Max | Unit |
|--------------------------------------|-----------------|------|------|-----|------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | -    | -    | 1.4 | °C/W |

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**Electrical Characteristics(T<sub>J</sub>=25°C unless otherwise noted)**

| OFF CHARACTERISTICS             |                   |   |      |      |      |      |
|---------------------------------|-------------------|---|------|------|------|------|
| Parameter                       | Symbol            | Conditions                                  | Min. | Typ. | Max. | Unit |
| Drain-Source Breakdown Voltage  | BV <sub>DSS</sub> | V <sub>GS</sub> =0V, I <sub>DS</sub> =250uA | 60   | -    | -    | V    |
| Zero Gate Voltage Drain Current | I <sub>DSS</sub>  | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V   | -    | -    | 1.0  | uA   |
| Gate-Body Leakage               | I <sub>GSS</sub>  | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V  | -    | -    | ±100 | nA   |

| ON CHARACTERISTICS               |                     |   |      |      |      |      |
|----------------------------------|---------------------|---|------|------|------|------|
| Parameter                        | Symbol              | Conditions  | Min. | Typ. | Max. | Unit |
| Gate Threshold Voltage           | V <sub>GS(TH)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250uA | 2    | 3    | 4    | V    |
| Drain-Source On-State Resistance | R <sub>DS(ON)</sub> | V <sub>GS</sub> =10V, I <sub>DS</sub> =30A                | -    | 12   | 20   | mΩ   |
|                                  |                     | V <sub>GS</sub> =4.5V, I <sub>DS</sub> =20A               | -    | 16   |      | mΩ   |

| DYNAMIC CHARACTERISTICS      |                  |   |      |      |      |      |
|------------------------------|------------------|---|------|------|------|------|
| Parameter                    | Symbol           | Conditions  | Min. | Typ. | Max. | Unit |
| Input Capacitance            | C <sub>ISS</sub> | V <sub>DS</sub> =25V, V <sub>GS</sub> = 0V,<br>f=1MHz | -    | 1300 | -    | pF   |
| Output Capacitance           | C <sub>OSS</sub> |   | -    | 300  | -    |      |
| Reverse Transfer Capacitance | C <sub>rss</sub> |   | -    | 105  | -    |      |

| SWITCHING CHARACTERISTICS     |                     |  |      |      |      |      |
|-------------------------------|---------------------|--|------|------|------|------|
| Parameter                     | Symbol              | Conditions   | Min. | Typ. | Max. | Unit |
| Turn-On Delay Time            | T <sub>d(on)</sub>  | V <sub>GS</sub> =10V, V <sub>DS</sub> =30V,<br>R <sub>GEN</sub> =4.7Ω<br>I <sub>D</sub> =27.5A | -    | 20   | -    | ns   |
| Rise Time                     | t <sub>r</sub>      |  | -    | 50   | -    |      |
| Turn-Off Delay Time           | T <sub>d(off)</sub> |  | -    | 36   | -    |      |
| Fall Time                     | t <sub>f</sub>      |  | -    | 15   | -    |      |
| Total Gate Charge at 10V      | Q <sub>g</sub>      | V <sub>DS</sub> =30V, I <sub>DS</sub> =55A,<br>V <sub>GS</sub> =10V                            | -    | 44.5 | 60   | nC   |
| Gate to Source Gate Charge    | Q <sub>gs</sub>     |  | -    | 10.5 | -    |      |
| Gate to Drain "Miller" Charge | Q <sub>gd</sub>     |  | -    | 17.5 | -    |      |

| DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS |                 |   |               |      |      |      |
|--|-----------------|---|---------------|------|------|------|
| Parameter  | Symbol          | Conditions                                | Min.          | Typ. | Max. | Unit |
| Drain-Source Diode Forward Voltage                     | V <sub>SD</sub> | V <sub>GS</sub> =0V, I <sub>DS</sub> =35A | -             | -    | 1.5  | V    |
| Reverse Recovery Time                                  | t <sub>rr</sub> | T <sub>J</sub> =25°C, I <sub>F</sub> =25A | -             | 75   | -    | nS   |
| Reverse Recovery Charge                                | Q <sub>rr</sub> |   | di/dt=100A/us | -    | 170  | -    |

**Notes:**

- 1: Repetitive rating, pulse width limited by maximum junction temperature.
- 2: Surface mounted on FR4 Board, t<sub>s</sub>≤10sec.
- 3: Pulse width ≤ 300μs, duty cycle ≤ 2%.
- 4: EAS condition: L=0.5mH, VDD=10V, VG=10V, V<sub>GATE</sub>=20V, Start T<sub>J</sub>=25°C.

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Figure 1: Output Characteristics

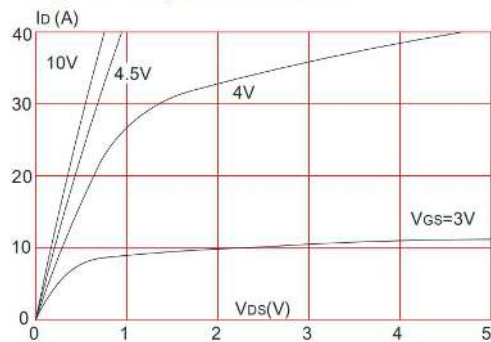


Figure 2: Typical Transfer Characteristics

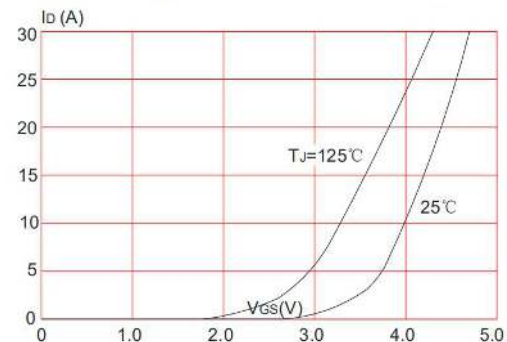


Figure 3: On-resistance vs. Drain Current

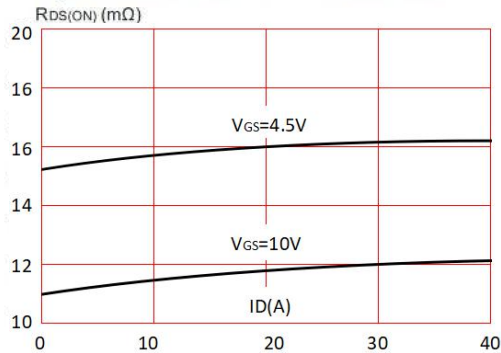


Figure 4: Body Diode Characteristics

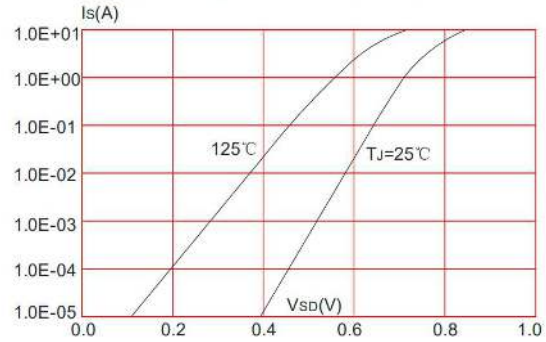


Figure 5: Gate Charge Characteristics

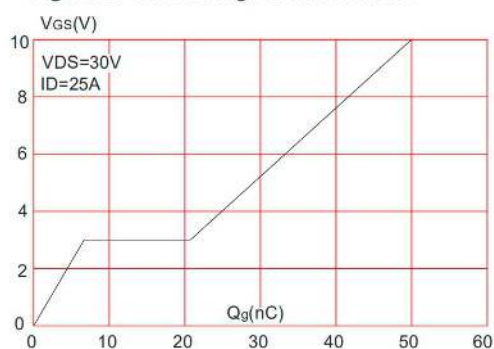
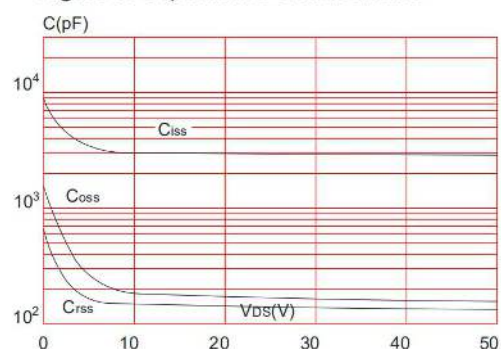
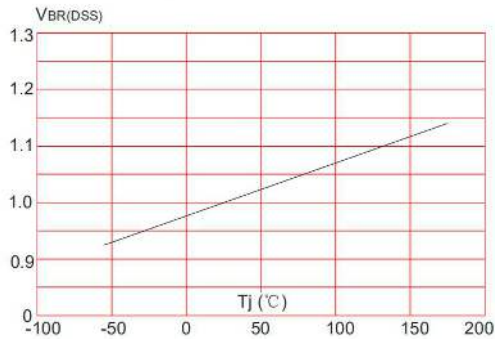


Figure 6: Capacitance Characteristics

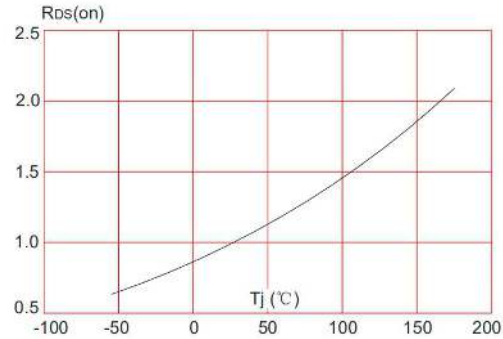


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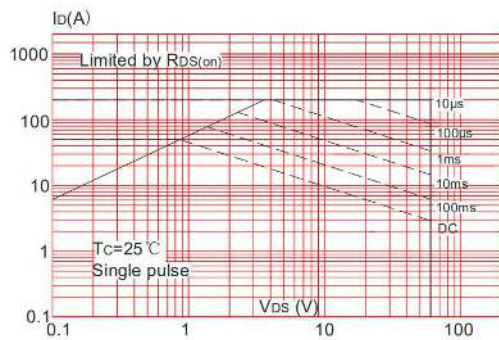
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



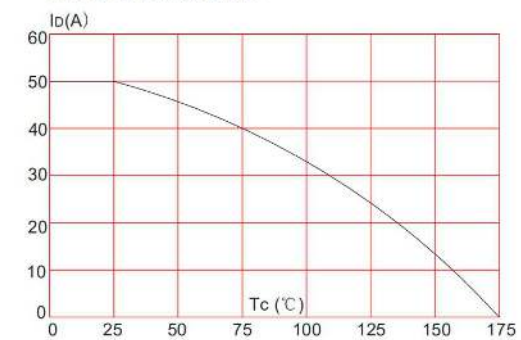
**Figure 8:** Normalized on Resistance vs. Junction Temperature



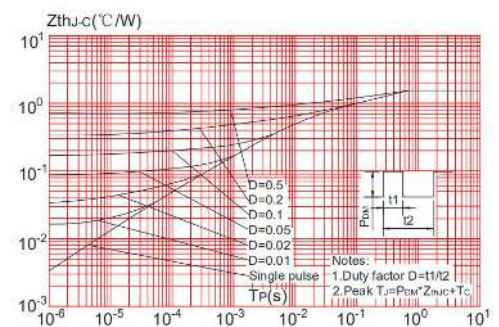
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case



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Test Circuit

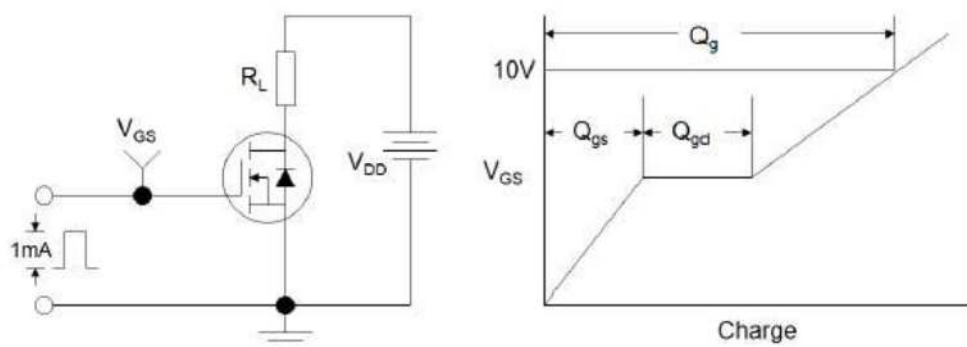


Figure1:Gate Charge Test Circuit & Waveform

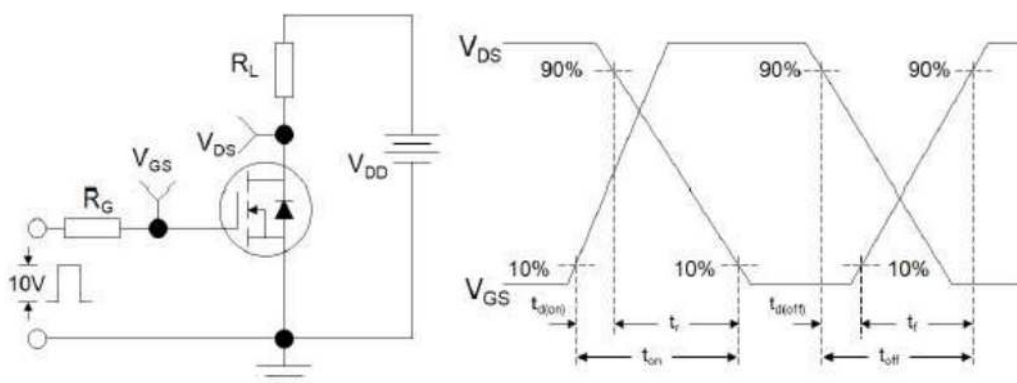


Figure 2: Resistive Switching Test Circuit & Waveforms

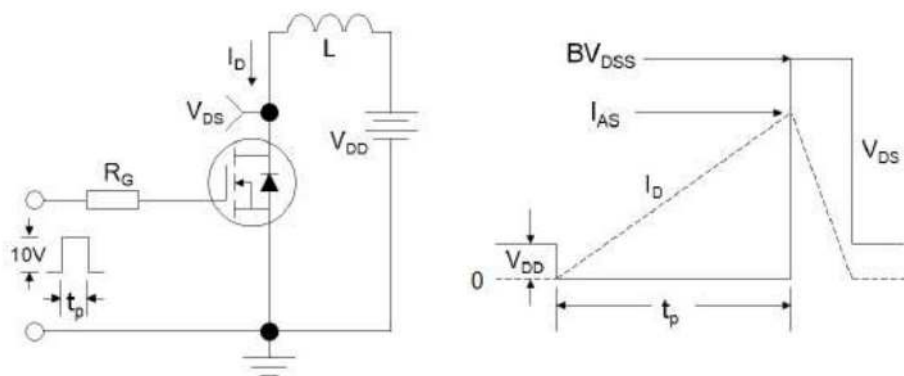
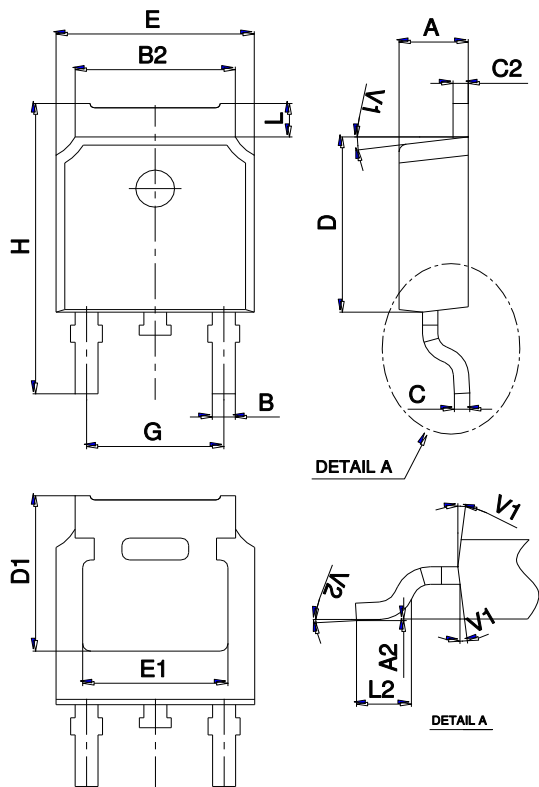


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data TO-252



| Ref. | Dimensions  |      |       |          |      |       |
|------|-------------|------|-------|----------|------|-------|
|      | Millimeters |      |       | Inches   |      |       |
|      | Min.        | Typ. | Max.  | Min.     | Typ. | Max.  |
| A    | 2.10        |      | 2.50  | 0.083    |      | 0.098 |
| A2   | 0           |      | 0.10  | 0        |      | 0.004 |
| B    | 0.66        |      | 0.86  | 0.026    |      | 0.034 |
| B2   | 5.18        |      | 5.48  | 0.202    |      | 0.216 |
| C    | 0.40        |      | 0.60  | 0.016    |      | 0.024 |
| C2   | 0.44        |      | 0.58  | 0.017    |      | 0.023 |
| D    | 5.90        |      | 6.30  | 0.232    |      | 0.248 |
| D1   | 5.30REF     |      |       | 0.209REF |      |       |
| E    | 6.40        |      | 6.80  | 0.252    |      | 0.268 |
| E1   | 4.63        |      |       | 0.182    |      |       |
| G    | 4.47        |      | 4.67  | 0.176    |      | 0.184 |
| H    | 9.50        |      | 10.70 | 0.374    |      | 0.421 |
| L    | 1.09        |      | 1.21  | 0.043    |      | 0.048 |
| L2   | 1.35        |      | 1.65  | 0.053    |      | 0.065 |
| V1   |             | 7°   |       |          | 7°   |       |
| V2   | 0°          |      | 6°    | 0°       |      | 6°    |

Ordering information

| Order code     | Package | Baseqty | Delivery mode |
|----------------|---------|---------|---------------|
| UMW STD35NF06L | TO-252  | 2500    | Tape and reel |